

Abstract of the Disclosure

A method of forming a MOS or CMOS device on a silicon substrate, includes preparing a substrate to contain conductive regions having device active areas therein; forming a gate electrode on the active
5 areas; depositing and forming a gate electrode sidewall insulator layer on each gate electrode; implanting ions of a first type to form a source region and a drain region in one active area and implanting ions of a second type to form a source region and a drain region in the other active area.